EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L2	622	257/335,339,340,409.ccor.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/02 11:59
L4	3169	257/E29.256,E29.257,E21.417,E21.418.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/02 12:27
L6	1877	@ad<"20000728" and L4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/02 12:37
L7	33888	Hwang.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/02 12:37
L8	5853	DMOS DMOSFET	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/02 12:37
L9	11	L7 and L8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/02 12:50
L10	1	(257/335,E29.256,E29.257,E21.417, E21.418 438/140).ccls. and (high adj voltage and source near12 trench near8 (poly polycrystalline polysilicon polysi) and high adj density adj diffusion and drift adj region and second near4 trench). clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/02 12:55

S1	1	@pn="6706567"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/02 12:27
S17	5	@ad<"20000728" and S16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/02 12:29
S21	18	438/140.ccor. and @ad<"20000728"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/25 13:21
S43	281	438/140,203,259,286,335.ccor. and @ad<"20000728"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/25 13:20
S44	236	257/335,339,340,409.ccor. and @ad<"20000728"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/07/02 11:59
S45	1	@pn="5869875"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/25 12:32
S46	594	438/140,203,259,286,335.ccor.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/25 13:21
S47	281	S46 and @ad<"20000728"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/06/25 13:21